



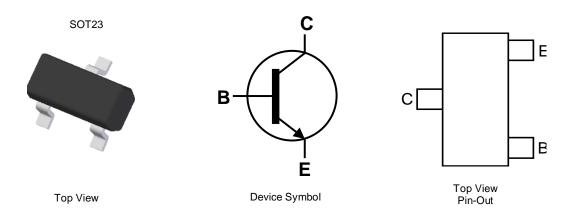
40V NPN SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary PNP Type: MMBT4403
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT23
- Package material: molded Plastic "Green" Compound UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



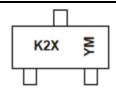
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT4401-7-F	Standard	K2X	7	8	3,000
MMBT4401-13-F	Standard	K2X	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K2X = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: I = 2021) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

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Year	2010		2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Х			J	K	L	М	N	0	Р	R	S
Month	la.	Fa.b	Man	A	Mari	l	ll	Aug	Son	Oct	Nov	Doc
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Absolute Maximum Ratings (@ T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current	Ic	600	mA
Peak Collector Current	Ісм	1	Α
Peak Base Current	I _{BM}	200	mA

Thermal Characteristics (@TA = +25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	310	mW	
Power dissipation	(Note 6)	P _D	350	IIIVV	
Thormal Basistanas, Jungtian to Ambient	(Note 5)	В	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	357	-0/00	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{ heta JL}$	350	°C/W	
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	120	°C/W	
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

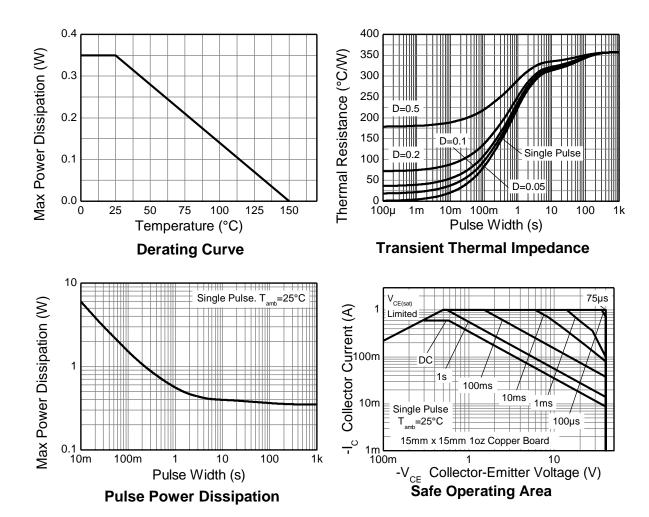
- 5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 15 mm x 15mm 1oz copper.

 7. Thermal resistance from junction to solder-point (at the end of the leads).

 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@ T_A = +25°C unless otherwise specified)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV _{CBO}	60	_	V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage(Note 9)	BV _{CEO}	40	_	V	$I_C = 10.0 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	ICEX	_	100	nA	$V_{CE} = 35V$, $V_{EB(OFF)} = 0.4V$
Base Cutoff Current	I _{BL}	_	100	nA	$V_{CE} = 35V, V_{EB(OFF)} = 0.4V$
ON CHARACTERISTICS (Note 9)					
DC Current Gain	h _{FE}	20 40 80 100 40		_	$\begin{split} I_C &= 100 \mu A, V_{CE} = 1.0 V \\ I_C &= 1.0 m A, V_{CE} = 1.0 V \\ I_C &= 10 m A, V_{CE} = 1.0 V \\ I_C &= 150 m A, V_{CE} = 1.0 V \\ I_C &= 500 m A, V_{CE} = 2.0 V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.40 0.75	V	$I_C = 150$ mA, $I_B = 15$ mA $I_C = 500$ mA, $I_B = 50$ mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	0.75 —	0.95 1.2	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{cb}	_	6.5	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$
Input Capacitance	C _{eb}		30	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$
Input Impedance	h _{ie}	1.0	15	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	8.0	x 10 ⁻⁴	V _{CE} = 10V, I _C = 1.0mA,
Small Signal Current Gain	h _{fe}	40	500	_	f = 1.0kHz
Output Admittance	h _{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f _T	250	_	MHz	V _{CE} = 10V, I _C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	_	15	ns	$V_{CC} = 30V, I_{C} = 150mA,$
Rise Time	t _r	_	20	ns	$V_{BE(off)} = 2.0V, I_{B1} = 15mA$
Storage Time	ts		225	ns	V _{CC} = 30V, I _C = 150mA,
Fall Time	t _f	_	30	ns	$I_{B1} = -I_{B2} = 15\text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



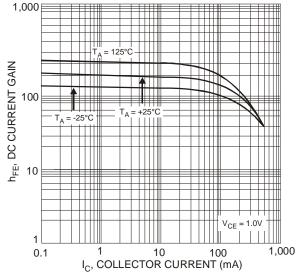
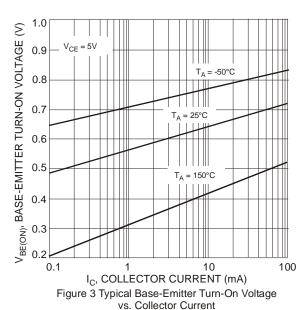


Figure 1 Typical DC Current Gain vs. Collector Current



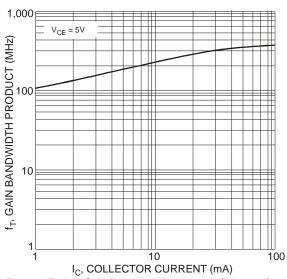


Figure 5 Typical Gain Bandwidth Product vs. Collector Current

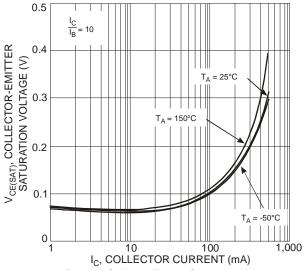


Figure 2 Collector-Emitter Saturation Voltage vs. Collector Current

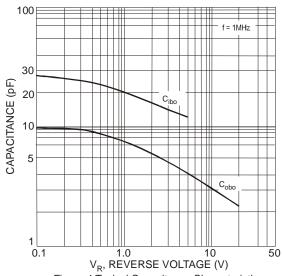


Figure 4 Typical Capacitance Characteristics

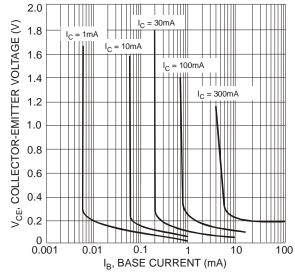


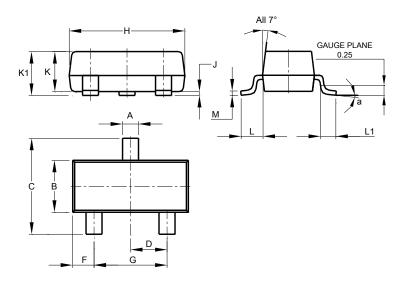
Figure 6 Typical Collector Saturation Region



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

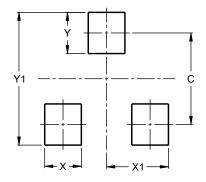


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	0°	8°			
All	Dimens	ions in	mm		

Suggested Pad Layout

 $Please\ see\ http://www.diodes.com/package-outlines.html\ for\ the\ latest\ version.$

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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